

1. General description

Ultrafast power diode in a SOD113 (2-lead TO-220F) plastic package.

2. Features and benefits

- Fast switching
- Isolated plastic package
- Low leakage current
- Low forward voltage drop
- Low thermal resistance
- Soft recovery characteristic
- Enhanced avalanche energy capability

3. Applications

- High frequency switched-mode power supplies
- Discontinuous Current Mode (DCM) Power Factor Correction (PFC)

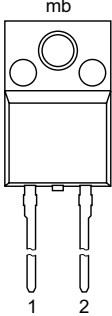
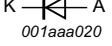
4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit
Absolute maximum rating						
V_{RRM}	repetitive peak reverse voltage		600			V
$I_{F(AV)}$	average forward current	$\delta = 0.5$; square-wave pulse; $T_h \leq 71$ °C; Fig. 1 ; Fig. 2 ; Fig. 3	10			A
I_{FRM}	repetitive peak forward current	$\delta = 0.5$; $t_p = 25$ μ s; $T_h \leq 71$ °C; square-wave pulse	20			A
I_{FSM}	non-repetitive peak forward current	$t_p = 10$ ms; $T_{j(init)} = 25$ °C; sine-wave pulse; Fig. 4	75			A
		$t_p = 8.3$ ms; $T_{j(init)} = 25$ °C; sine-wave pulse;	83			A
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
V_F	forward voltage	$I_F = 10$ A; $T_j = 25$ °C; Fig. 6	-	1.55	2	V
		$I_F = 10$ A; $T_j = 150$ °C; Fig. 6	-	-	1.6	V
Dynamic characteristics						
t_{rr}	reverse recovery time	$I_F = 1$ A; $V_R = 30$ V; $di_F/dt = 50$ A/ μ s; $T_j = 25$ °C; Fig. 7	-	35	50	ns
		$I_F = 10$ A; $V_R = 200$ V; $di_F/dt = 200$ A/ μ s; $T_j = 25$ °C; Fig. 7	-	50	-	ns
		$I_F = 10$ A; $V_R = 200$ V; $di_F/dt = 200$ A/ μ s; $T_j = 125$ °C; Fig. 7	-	78	-	ns
		$I_F = 10$ A; $V_R = 400$ V; $di_F/dt = 500$ A/ μ s; $T_j = 25$ °C; Fig. 7	-	42	-	ns

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		
2	A	anode		
mb	n.c.	mounting base; isolated		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BYV10EX-600P	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 "full pack"	SOD113

7. Marking

Table 4. Marking codes

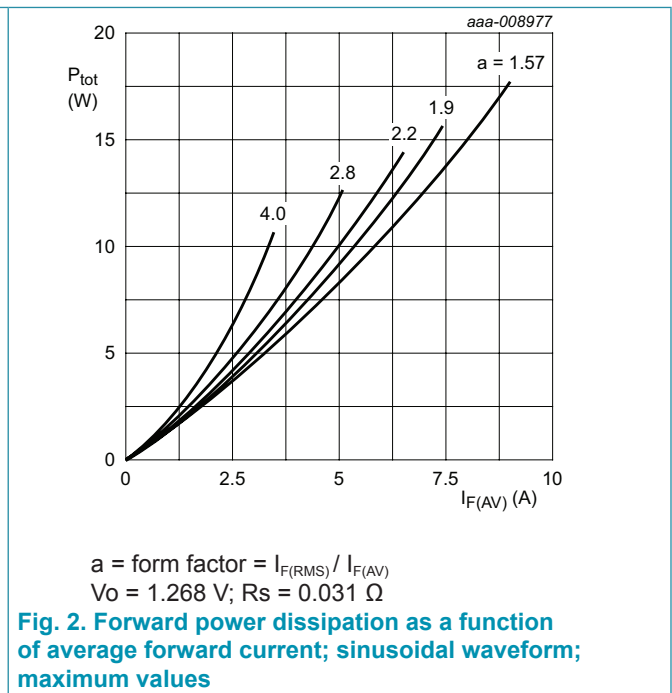
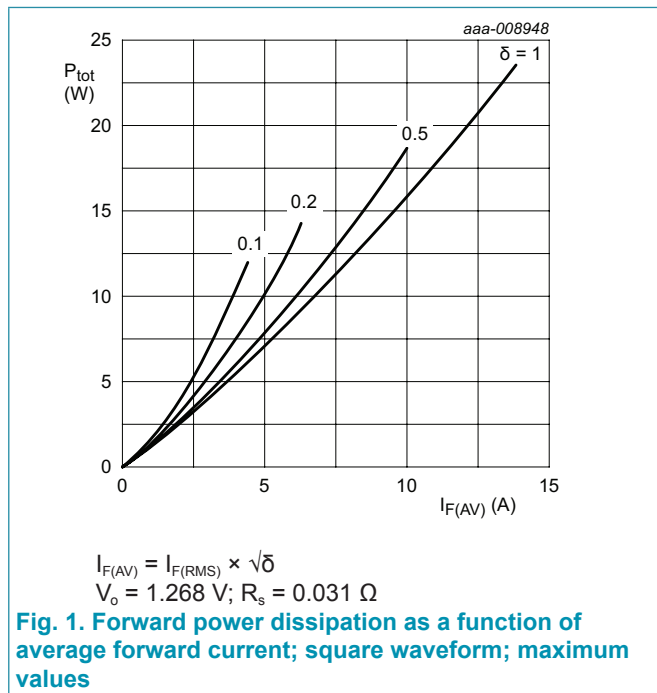
Type number	Marking codes
BYV10EX-600P	BYV10EX-600P

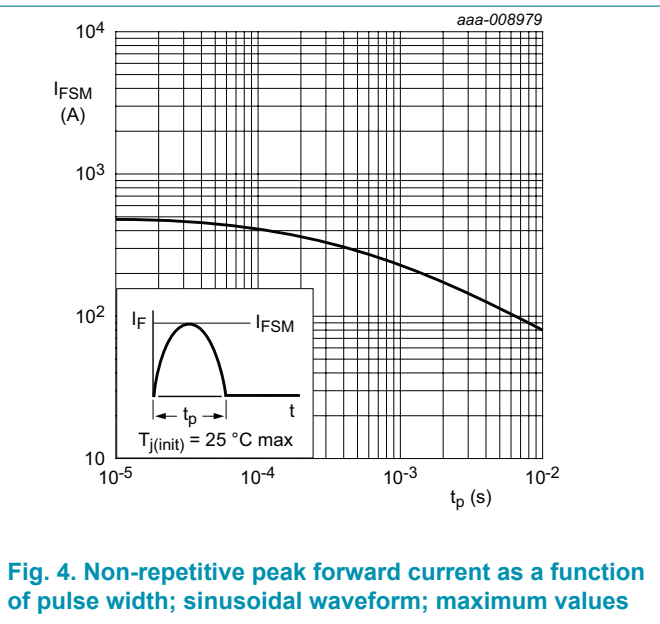
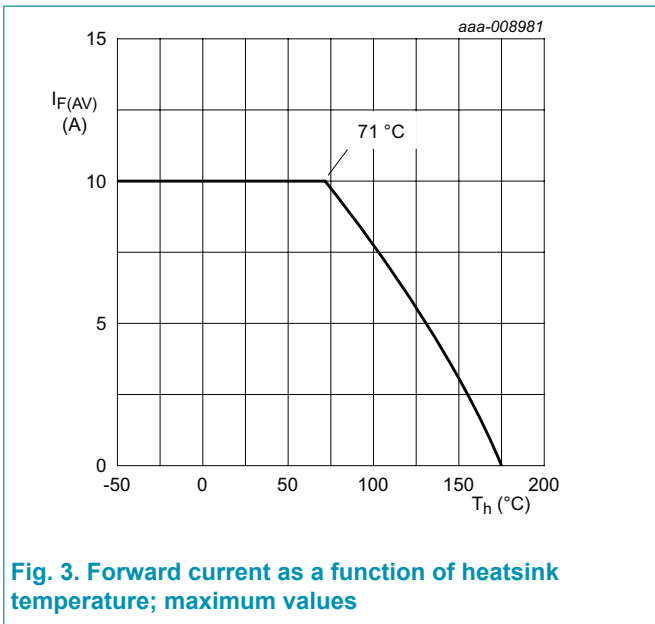
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		600	V
V_{RWM}	crest working reverse voltage		600	V
V_R	reverse voltage	DC	600	V
$I_{F(AV)}$	average forward current	$\delta = 0.5$; square-wave pulse; $T_h \leq 71$ °C; Fig. 1 ; Fig. 2 ; Fig. 3	10	A
I_{FRM}	repetitive peak forward current	$\delta = 0.5$; $t_p = 25$ μ s; $T_h \leq 71$ °C; square-wave pulse	20	A
I_{FSM}	non-repetitive peak forward current	$t_p = 10$ ms; $T_{j(init)} = 25$ °C; sine-wave pulse; Fig. 4	75	A
		$t_p = 8.3$ ms; $T_{j(init)} = 25$ °C; sine-wave pulse;	83	A
T_{stg}	storage temperature		-65 to 175	°C
T_j	junction temperature		175	°C





9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	With heatsink compound; Fig. 5	-	-	5.5	K/W
		Without heatsink compound	-	-	7.2	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air	-	55	-	K/W

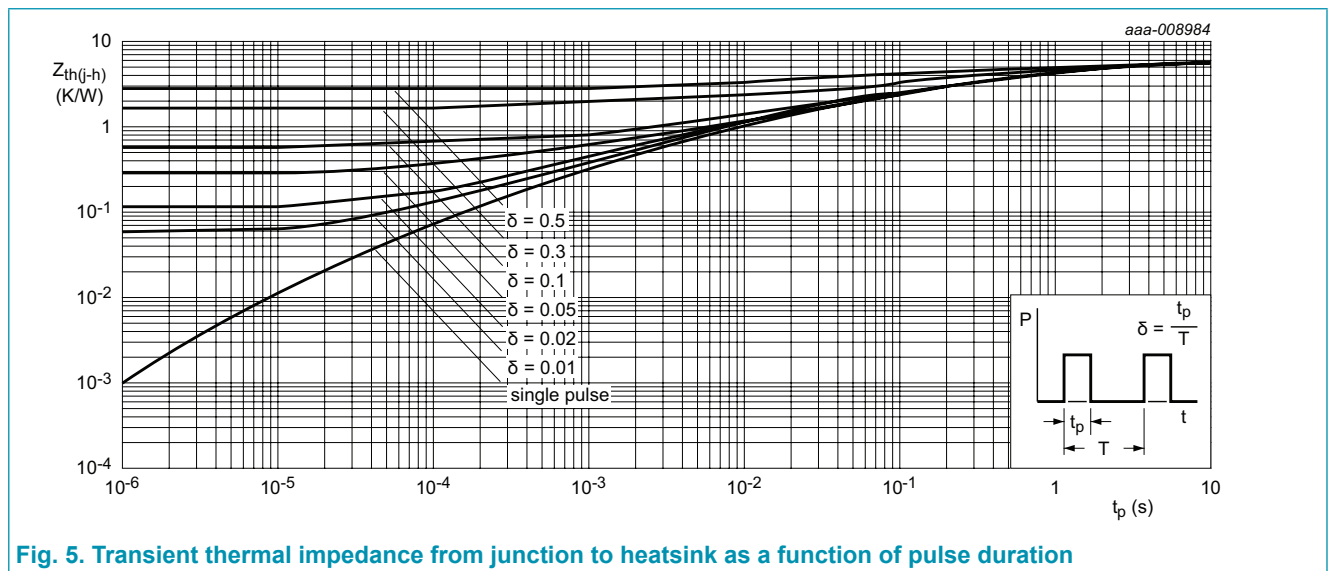


Fig. 5. Transient thermal impedance from junction to heatsink as a function of pulse duration

10. Isolation characteristics

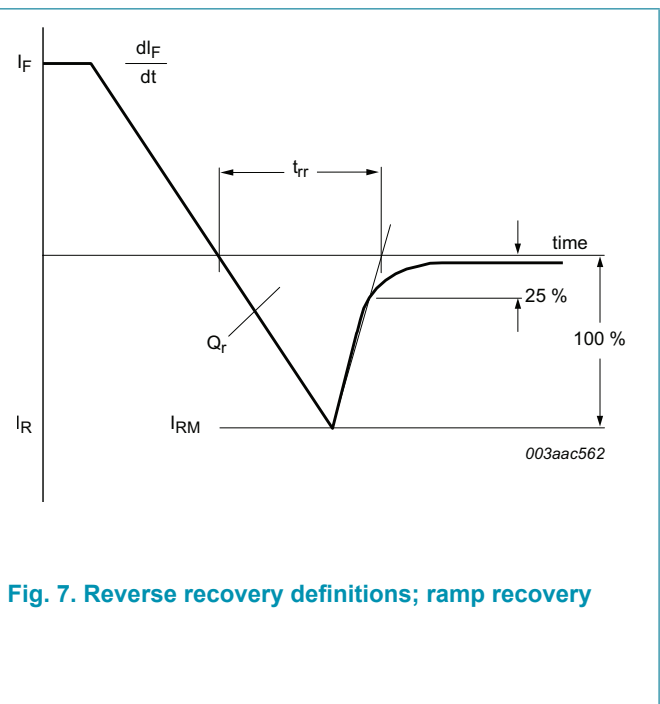
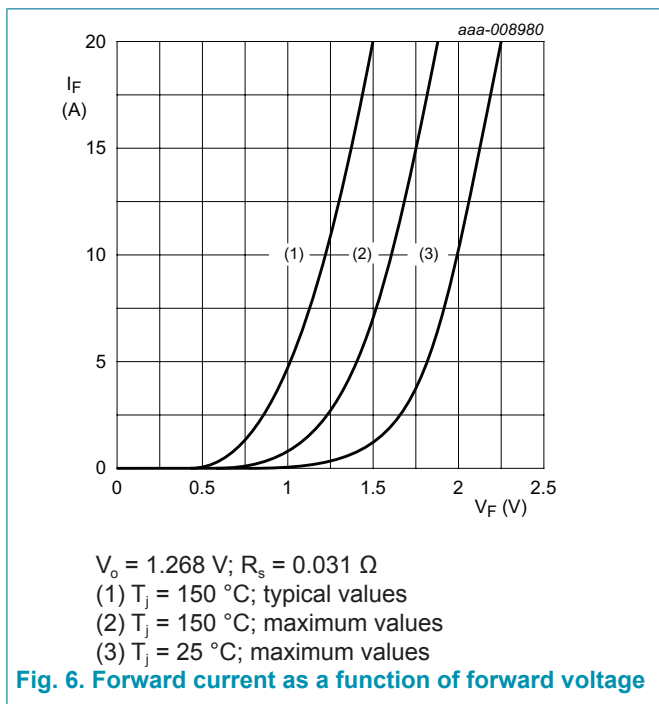
Table 6. Isolation characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{isol(RMS)}$	RMS isolation voltage	50 Hz ≤ f ≤ 60 Hz; RH ≤ 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
C_{isol}	isolation capacitance	from cathode to external heatsink	-	10	-	PF

11. Characteristics

Table 7. Characteristics

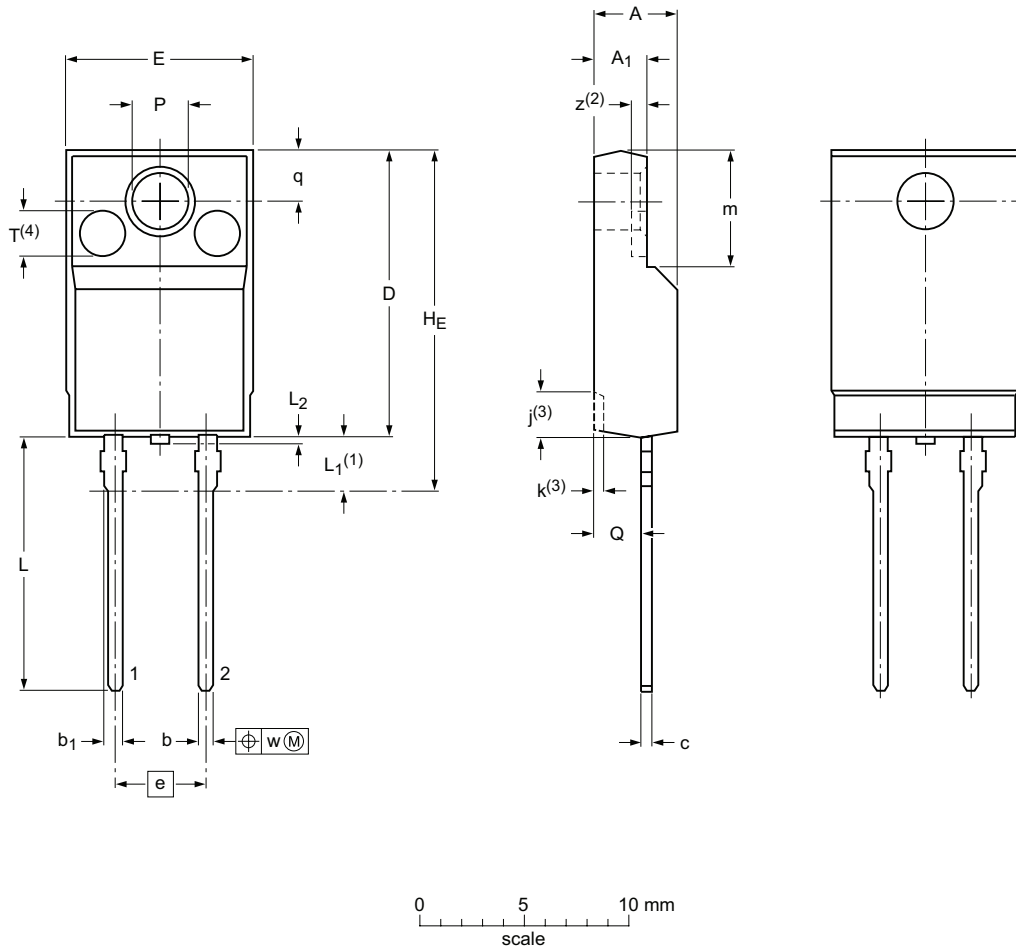
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
V_F	forward current	$I_F = 10 \text{ A}; T_j = 25 \text{ }^\circ\text{C}; \text{Fig. 6}$	-	1.55	2	V
		$I_F = 10 \text{ A}; T_j = 150 \text{ }^\circ\text{C}; \text{Fig. 6}$	-	-	1.6	V
I_R	reverse current	$V_R = 600 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	-	10	μA
		$V_R = 600 \text{ V}; T_j = 150 \text{ }^\circ\text{C}$	-	-	250	μA
Dynamic characteristics						
Q_r	reverse charge	$I_F = 10 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s}; T_j = 25 \text{ }^\circ\text{C}; \text{Fig. 7}$	-	123	-	nC
		$I_F = 10 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s}; T_j = 125 \text{ }^\circ\text{C}; \text{Fig. 7}$	-	305	-	nC
t_{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A}/\mu\text{s}; T_j = 25 \text{ }^\circ\text{C}; \text{Fig. 7}$	-	35	50	ns
		$I_F = 10 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s}; T_j = 25 \text{ }^\circ\text{C}; \text{Fig. 7}$	-	50	-	ns
		$I_F = 10 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s}; T_j = 125 \text{ }^\circ\text{C}; \text{Fig. 7}$	-	78	-	ns
		$I_F = 10 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s}; T_j = 25 \text{ }^\circ\text{C}; \text{Fig. 7}$	-	42	-	ns
I_{RM}	peak reverse recovery current	$I_F = 10 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s}; T_j = 25 \text{ }^\circ\text{C}; \text{Fig. 7}$	-	4.9	-	A
		$I_F = 10 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s}; T_j = 125 \text{ }^\circ\text{C}; \text{Fig. 7}$	-	7.8	-	A
E_{as}	non-repetitive avalanche energy	$I_R = 1.2 \text{ A}; T_{j(\text{init})} = 25 \text{ }^\circ\text{C}; L = 15 \text{ mH}$	10.8	-	-	mJ



12. Package outline

Plastic single-ended package; isolated heatsink mounted;
1 mounting hole; 2-lead TO-220 `full pack`

SOD113



Dimensions (mm are the original dimensions)

Unit	A	A ₁	b	b ₁	c	D	E	e	H _E max	j ⁽³⁾	k ⁽³⁾	L	L ₁ ⁽¹⁾	L ₂ max	m	P	Q	q	T ⁽⁴⁾	w	z ⁽²⁾	
max	4.6	2.9	0.9	1.1	0.7	15.8	10.3		19.0	2.7	0.6	14.4	3.3	0.5	6.5	3.2	2.6		2.6	2.55	0.4	0.8
nom								5.08														
min	4.0	2.5	0.7	0.9	0.4	15.2	9.7			1.7	0.4	13.5	2.8		6.3	3.0	2.3					

Notes

1. Terminals are uncontrolled within zone L1.
2. z is depth of T.
3. Dot lines area designs may vary.
4. Eject pin mark is for reference only.

sod113_po

Outline version	References			European projection	Issue date
	IEC	JEDEC	JEITA		
SOD113		2-lead TO-220F			07-06-08 15-08-28

Fig. 8. Package outline SOD113 (TO-220F)

13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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